



MDL-XN-8200/1-1300mW



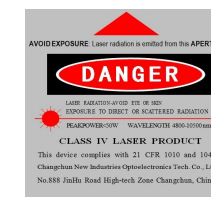
**INFRARED QCL DIODE
LASER AT 8200nm**

It features ultra compact design, long lifetime, cost-effectiveness and easy operation. They are widely used in measurement, communication, spectrum analysis, etc.

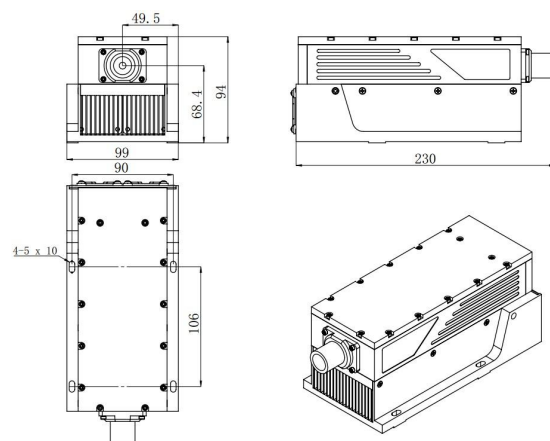


SPECIFICATIONS

Central wavelength (μm)	8.2±0.3
Operating mode	CW
Output power (mW) ¹	1-1300
Power stability (rms, 4 hours ± 3°C)	<3%, <2%, <1%
Transverse mode	Near TEM ₀₀
Beam diameter at the aperture (mm)	<3.0
Beam divergence, full angle (mrad)	<5.0
Warm-up time (minutes)	<10
Cooled method	Air cooled
Beam height from base plate (mm)	68.4
Operating temperature (°C)	10-35
Power supply (100-240VAC)	PSU-H-LED
Modulation option	DC-1kHz; TTL and Analog optional
Expected lifetime (hours)	>10000

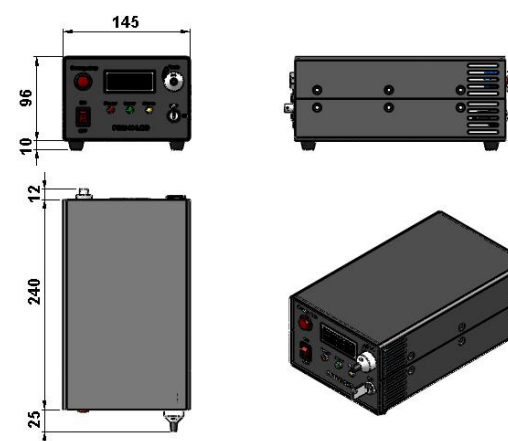


LASER HEAD



230 (L) × 99 (W) × 94 (H) mm³, 3.0kg

POWER SUPPLY²



277 (L) × 145 (W) × 106 (H) mm³, 2.3kg

¹ Any power level can be selected in this range.

² Output power adjustable 10-100%; RS232 control optional.